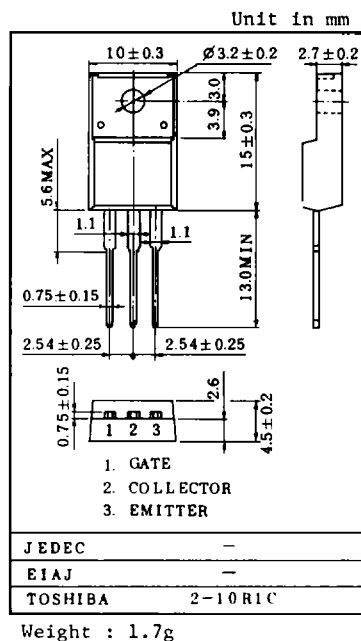
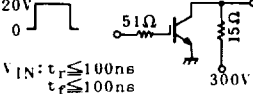


- . High Input Impedance
- . Low Saturation Voltage : $V_{CE(sat)}=8V(Max.)$ ($I_C=130A$)
- . Enhancement-Mode
- . 20V Gate Drive

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		V _{CES}	400	V
Gate-Emitter Voltage		V _{GES}	±25	V
Collector Current	DC	I _C	10	A
	1ms	I _{CP}	130	
Collector Power Dissipation	T _a =25°C	P _C	2.0	W
	T _c =25°C	P _C	30	
Junction Temperature		T _j	150	°C
Storage Temperature Range		T _{stg}	-55~150	°C
Screw Torque		-	0.6	N·m



CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GES}	$V_{GE}=\pm 25V, V_{CE}=0$	-	-	± 100	nA
Collector Cut-off Current		I_{CES}	$V_{CE}=400V, V_{GE}=0$	-	-	10	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)CES}$	$I_C=2mA, V_{GE}=0$	400	-	-	V
Gate-Emitter Cut-off Voltage		$V_{GE(OFF)}$	$I_C=1mA, V_{CE}=5V$	4	5	7	V
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C=130A$ $V_{GE}=20V$ (Pulsed)	-	5	8	V
Input Capacitance		C_{ies}	$V_{CE}=10V, V_{GE}=0, f=1MHz$	-	1350	-	pF
Switching Time	Rise Time	t_r	 $V_{IN}: t_r \leq 100ns$ $t_f \leq 100ns$ duty cycle $\leq 1\%$	-	0.1	0.5	μs
	Turn-on Time	t_{on}		-	0.15	0.5	
	Fall Time	t_f		-	4.0	6.0	
	Turn-off Time	t_{off}		-	4.5	7.0	
Thermal Resistance		$R_{th(j-c)}$	-	-	-	4 16	$^{\circ}C/W$

